

# Tunable electronic structure of few-layer graphene with pressure



Lei Mu<sup>1</sup>, Shenyang Huang<sup>1</sup>, Qiaoxia Xing<sup>1</sup>, Chong Wang<sup>1</sup>, Yanlin Mou<sup>1</sup>, Yuchen Lei<sup>1</sup>, Yuangang Xie<sup>1</sup>, Jiasheng Zhang<sup>1</sup>, Junwei Ma<sup>1</sup>, Yixuan Ma<sup>1</sup>, Hugen Yan<sup>1,\*</sup>

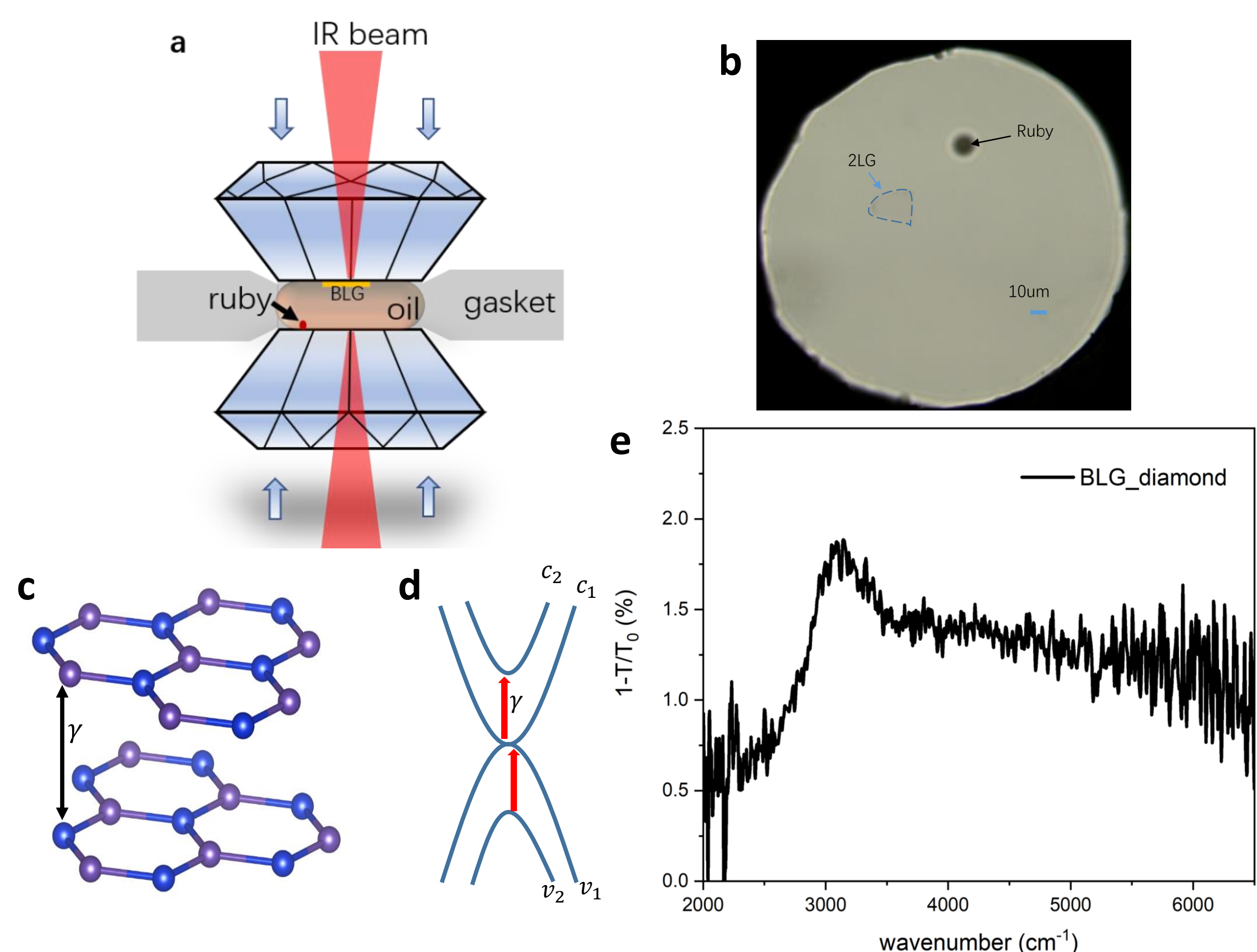
<sup>1</sup>State Key Laboratory of Surface Physics and Department of Physics, Fudan University, Shanghai 200433, China.

FDU Annual Academic Conference of Dept. Physics (2023)

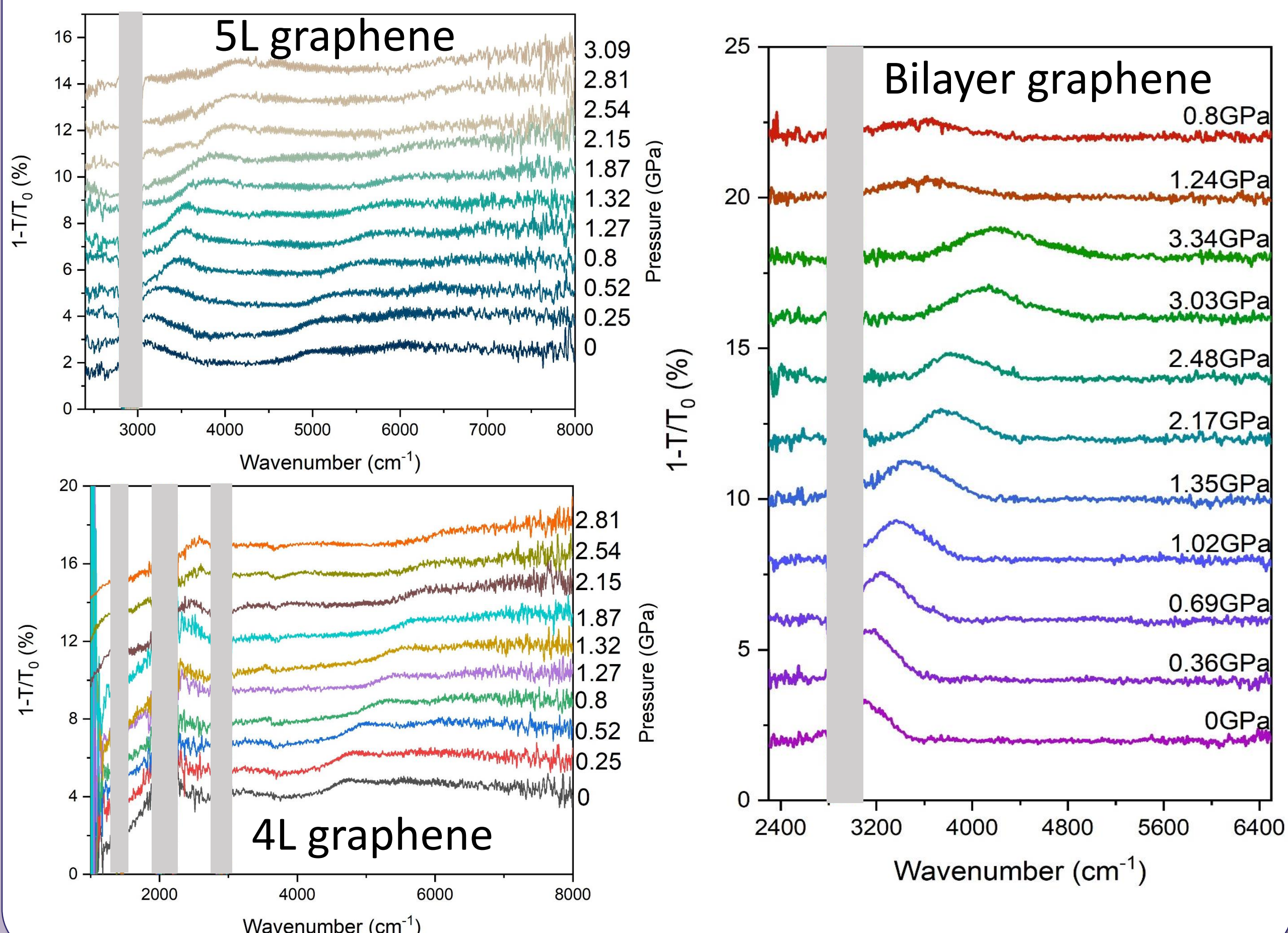
## Introduction

The superior physical properties of graphene make it a promising material. Recently, there is an alternative approach of tuning the interlayer interaction of few layer graphene with pressure to modulate the electronic structure. However, the pressure-induced infrared responses of few layer graphene have not been reported experimentally to date. Here, we investigate the pressure effect on the band structure of 2L-8L graphene with ABA-stacked in a diamond anvil cell(DAC) through Fourier transform infrared spectroscopy. The pressure effect on the electronic structure of few-layer graphene can be explained by the tight-binding model in conjunction with a Morse potential. Our study paves a way for van der Waals engineering of few-layer graphene.

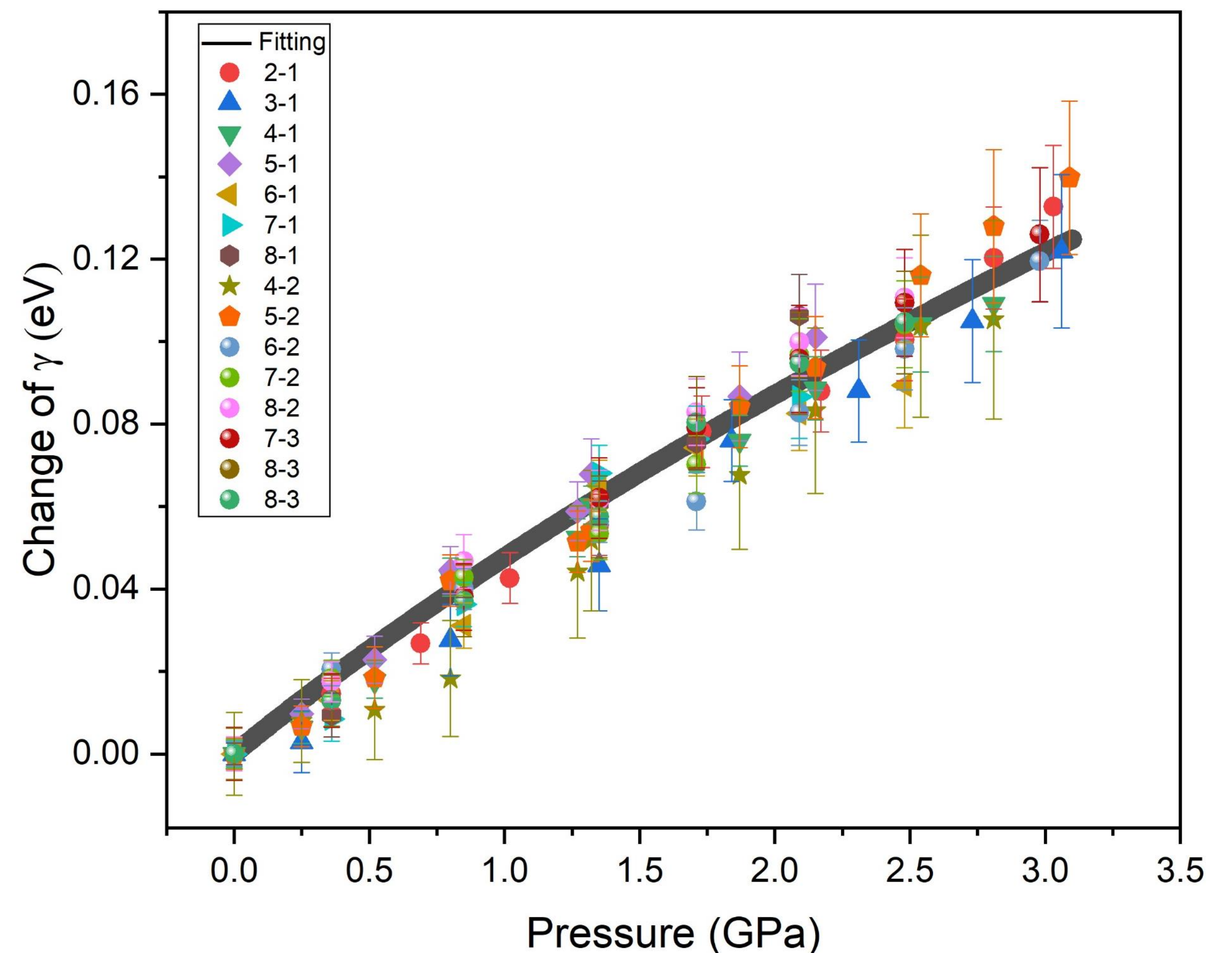
## Optical characterization of bilayer graphene in DAC



## Evolution of the band structure of graphene



## Layer-dependent pressure effect on graphene



➤ Layer-dependent optical transition energy of graphene:

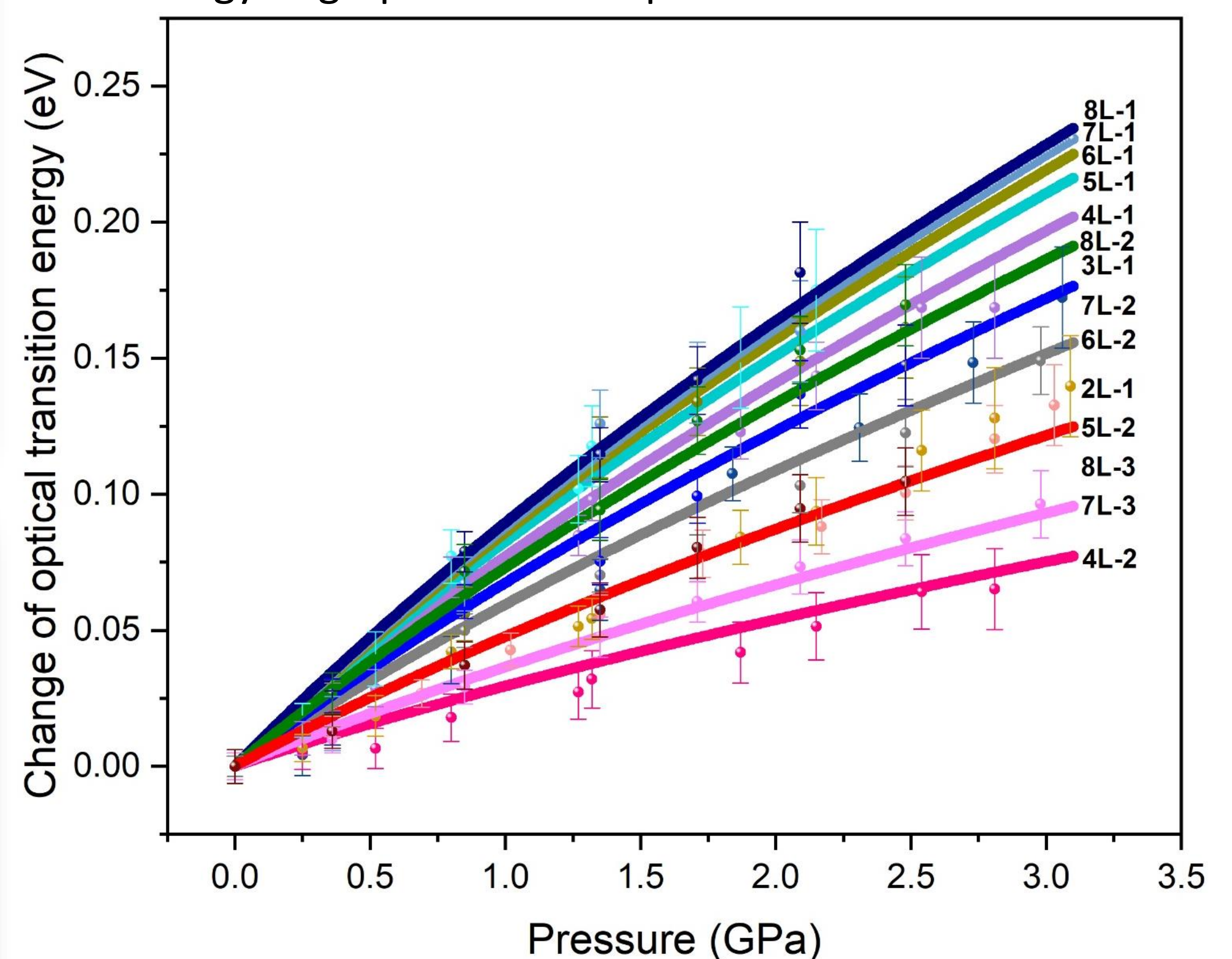
$$E(P) = 2\gamma(P) \cdot \cos\left(\frac{n\pi}{N+1}\right)$$

According to the Morse potential, the interlayer coupling strength  $\gamma(P)$  can be given by

$$\gamma(P) = \frac{\gamma_0}{2} \left(1 + \sqrt{1 + P/P_{coh}}\right)$$

where  $\gamma_0$  is interlayer coupling strength under 0GPa,  $P_{coh}$  is obtained as 1.74GPa through fitting datas.

➤ The relative changes of layer-dependent optical transition energy of graphene versus pressure as follows:



## Conclusion

We investigated the evolution of pressure-induced electronic structures of 2L-8L graphene experimentally in detail. In order to quantify evolution of optical transition energy with pressure, the tight-binding model and the Morse potential are applied. Our study revealed that with increasing pressure, the interlayer coupling of graphene is enhanced, the correspond optical transition energy can increase  $\sim 22\%$  up to 3GPa for 8LG.